

1 48. (Amended) A semiconductor processing method of chemical
2 vapor depositing SiO₂ on a substrate comprising:
3 placing a substrate within a hot wall low pressure chemical vapor
4 deposition reactor;
5 feeding an organic silicon precursor into the hot wall chemical
6 vapor deposition reactor having the substrate positioned therein [under
7 conditions effective to decompose the precursor into SiO₂ which deposits
8 on the substrate and into a gaseous oxide of hydrogen]; [and]
B
9 feeding an additional quantity of the gaseous oxide of hydrogen
10 into the hot wall low pressure chemical vapor deposition reactor while
11 feeding the organic silicon precursor into the reactor, wherein the
12 organic silicon precursor and the additional quantity of the gaseous oxide
13 of hydrogen are fed into the reactor from separate feed streams; and
14 providing conditions effective to decompose the precursor into SiO₂
15 at a theoretical decomposition rate and effective to cause the additional
16 quantity of gaseous oxide of hydrogen to reduce the theoretical
17 decomposition rate to a lower actual decomposition rate.

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19 **REMARKS**

20 Claims 43, 44, 46 and 48 are amended. Claim 48 is amended to
21 recite a "theoretical decomposition rate" and an "actual decomposition
22 rate." Such amendments are supported in the specification at page 7,
23 line 15 through page 10, line 2. A process providing for the